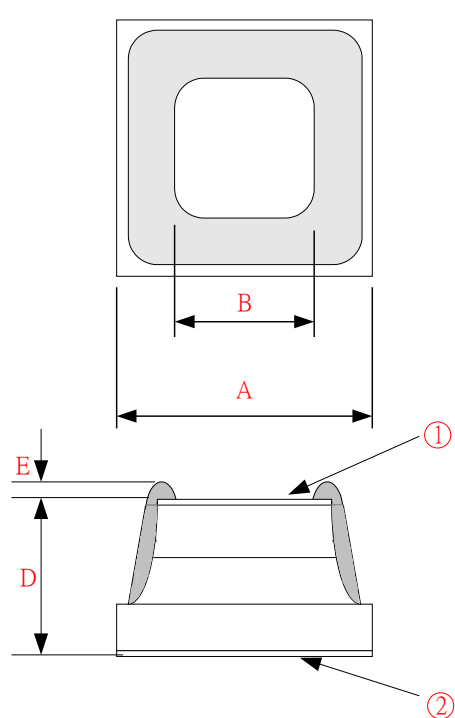


Product	Type									
<p style="text-align: center;">Ultra Fast Rectifier Diodes</p> <p style="text-align: center;">Top Au ①</p> <p style="text-align: center;">Bottom Au ②</p>										
<p>Dimension in mils</p> <table border="1" data-bbox="70 480 566 794"> <thead> <tr> <th></th> <th>Dimension</th> </tr> </thead> <tbody> <tr> <td>A</td> <td>195±2</td> </tr> <tr> <td>B</td> <td>169(min.)</td> </tr> <tr> <td>D</td> <td>10.5±1</td> </tr> <tr> <td>E</td> <td>1.5±1</td> </tr> </tbody> </table>			Dimension	A	195±2	B	169(min.)	D	10.5±1	E
	Dimension									
A	195±2									
B	169(min.)									
D	10.5±1									
E	1.5±1									

Absolute Maximum Ratings (Ta=25°C)

PEAK REVERSE VOLTAGE VRM .. 1000 V

FORWARD

SURGE CURRENT IFSM....350 A STORAGE TEMPERATURE RANGE Tstg .. -65~150°C

Electrical Characteristics

Item	Symbol	Test Condition	Standard
FORWARD VOLTAGE(for cell type)	VF	IF=40A	1.85 V (MAX)
REVERSE CURRENT	IR	VR=1000V	10µA (MAX)
REVERSE RECOVERY TIME	TRR	RG1	100ns
BREAKDOWN VOLTAGE	BVR	IR=10µA	1020V (MIN)

Quality Yield Assurance per wafer: 70%